SURFACE TREATMENT METHOD, DRY ETCHING METHOD, CLEANING METHOD, SEMICONDUCTOR DEVICE MANUFACTURING METHOD, AND ETCHING DEVICE

ABSTRACT

The purpose of the present disclosure is to provide a surface treatment method that uses a gas composition capable of removing metal nitrides without plasma and at low temperatures. The present disclosure is a surface treatment method characterized by bringing a β-diketone and NO_2 into contact with the surface of an object to be treated.

No suitable figure.